L Number	Hits	Search Text	DB	Time stamp
1	236	DRAM adj bit adj lines	USPAT	2003/04/13 12:52
2	0	(DRAM adj bit adj lines) and (chem-mech adj polishing) and	USPAT	2003/04/13 12:55
		(first adj insulating) and (second adj insulating) and (third adj	301741	2003/04/13 12.33
		insulating) and (fourth adj insulating) and (active adj region)		
		and opening and etchable		
3	0		LICDAT	0000000000
3		The second secon	USPAT	2003/04/13 12:58
		(first adj insulating) and (second adj insulating) and (third adj		
		insulating) and (fourth adj insulating) and (active adj region)		
		and opening		
4	0	(DRAM adj bit adj lines) and (chem-mech adj polishing) and	USPAT	2003/04/13 12:56
		(first adj insulating) and (second adj insulating) and (third adj		
		insulating) and (fourth adj insulating) and active and region		
_	_	and opening		
5	2	(DRAM adj bit adj lines) and (first adj insulating) and (second	USPAT	2003/04/13 13:07
		adj insulating) and (third adj insulating) and (fourth adj		
		insulating) and active and region and opening		
6	1	(DRAM adj bit adj lines) and (first adj insulating) and (second	USPAT	2003/04/13 12:59
		adj insulating) and (third adj insulating) and (fourth adj		
		insulating) and (active adj region) and opening and polishing		
7	2	((DRAM adj bit adj lines) and (first adj insulating) and (second	USPAT	2003/04/13 13:03
		adj insulating) and (third adj insulating) and (fourth adj	30.71	2000/04/10 10:00
		insulating) and active and region and opening) and (polishing		
		or mechanical or chemical or opening or hole or etch or		İ
		etching or etchable or conductive or lines or bit or word or line		!
		or source or drain or memory or material or structure or		
		substrate oe entire or trench or STI)		
8	2		LICDAT	0000/04/40 40 00
"		((DRAM adj bit adj lines) and (first adj insulating) and (second	USPAT	2003/04/13 13:39
1		adj insulating) and (third adj insulating) and (fourth adj	1	
		insulating) and active and region and opening) and (polishing		i
		or mechanical or chemical or opening or hole or etch or		
		etching or etchable or conductive or lines or bit or word or line		
		or source or drain or memory or material or structure or		
		substrate oe entire or trench or STI or silicon or nitride or		
		oxide)		
9	4	(DRAM adj bit adj lines) and (first adj insulating) and (second	USPAT	2003/04/13 13:27
		adj insulating) and (third adj insulating) and (fourth adj		
		insulating) and word and line and gate and active and region		
10	1		USPAT	2003/04/13 13:26
11	1		USPAT	2003/04/13 13:26
12	1		USPAT	2003/04/13 13:26
13	1		USPAT	2003/04/13 13:26
14	1		USPAT	2003/04/13 13:27
15	17	DRAM and STI and (first adj insulating) and (second adj	USPAT	2003/04/13 13:38
		insulating) and (third adj insulating) and (fourth adj insulating)	1	
		and word and line and gate and active and bit	1	
16	1	("6475858").PN.	USPAT	2003/04/13 13:39
17	1	(("6475858").PN.) and (polishing or mechanical or chemical or	USPAT	2003/04/13 13:51
	'	opening or hole or etch or etching or etchable or conductive or	JOPAI	2003/04/13 13.91
		lines or bit or word or line or source or drain or memory or		
		material or structure or substrate oe entire or trench or STI or		
10		silicon or nitride or oxide)	LICDAT	0000004/10 10 55
18	1		USPAT	2003/04/13 13:50
19	1		USPAT	2003/04/13 13:50
20	1		USPAT	2003/04/13 13:50
21	1		USPAT	2003/04/13 13:51
22	1	1 1/1	USPAT	2003/04/13 13:51
23	1		USPAT	2003/04/13 13:51
24	1	("5893734").PN.	USPAT	2003/04/13 13:52
25	1	("5400275").PN.	USPAT	2003/04/13 13:53
26	1	("5895239").PN.	USPAT	2003/04/13 13:53
27	1	("6083790").PN.	USPAT	2003/04/13 13:53
28	861	438/381	USPAT	2003/04/13 13:54
29	899	438/241	USPAT	2003/04/13 13:54
30	248	438/242	USPAT	2003/04/13 13:54
31	708	438/270	USPAT	2003/04/13 13:54
32	782	438/680	USPAT	2003/04/13 13:54
			JOEAT	2003/04/13 13.04